



# M48Z128 M48Z128Y

## 1 Mbit (128Kb x8) ZEROPOWER® SRAM

- INTEGRATED LOW POWER SRAM, POWER-FAIL CONTROL CIRCUIT and BATTERY
- CONVENTIONAL SRAM OPERATION; UNLIMITED WRITE CYCLES
- 10 YEARS of DATA RETENTION in the ABSENCE of POWER
- AUTOMATIC POWER-FAIL CHIP DESELECT and WRITE PROTECTION
- WRITE PROTECT VOLTAGES ( $V_{PFD}$  = Power-fail Deselect Voltage):
  - M48Z128:  $4.50V \leq V_{PFD} \leq 4.75V$
  - M48Z128Y:  $4.20V \leq V_{PFD} \leq 4.50V$
- BATTERY INTERNALLY ISOLATED UNTIL POWER IS APPLIED
- PIN and FUNCTION COMPATIBLE with JEDEC STANDARD 128K x 8 SRAMs
- SURFACE MOUNT CHIP SET PACKAGING INCLUDES a 28-PIN SOIC and a 32-LEAD TSOP (SNAPHAT TOP TO BE ORDERED SEPARATELY)
- SOIC PACKAGE PROVIDES DIRECT CONNECTION for a SNAPHAT TOP WHICH CONTAINS the BATTERY
- SNAPHAT® HOUSING (BATTERY) IS REPLACEABLE

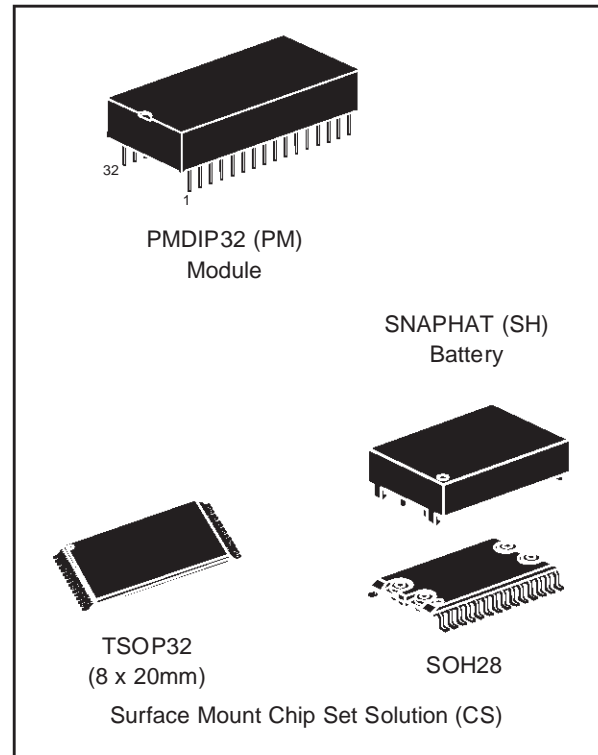


Figure 1. Logic Diagram

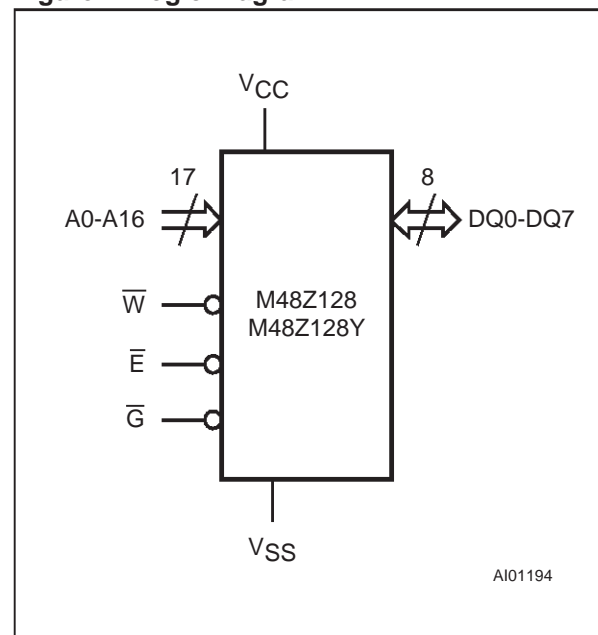


Table 1. Signal Names

A0-A16	Address Inputs
DQ0-DQ7	Data Inputs / Outputs
$\bar{E}$	Chip Enable
$\bar{G}$	Output Enable
$\bar{W}$	Write Enable
V <sub>CC</sub>	Supply Voltage
V <sub>SS</sub>	Ground
NC	Not Connected Internally

## M48Z128, M48Z128Y

**Table 2. Absolute Maximum Ratings <sup>(1)</sup>**

Symbol	Parameter	Value	Unit
T <sub>A</sub>	Ambient Operating Temperature	0 to 70	°C
T <sub>STG</sub>	Storage Temperature (V <sub>CC</sub> Off)	-40 to 70	°C
T <sub>BIAS</sub>	Temperature Under Bias	-10 to 70	°C
T <sub>SLD</sub> <sup>(2)</sup>	Lead Solder Temperature for 10 seconds	260	°C
V <sub>IO</sub>	Input or Output Voltages	-0.3 to 7	V
V <sub>CC</sub>	Supply Voltage	-0.3 to 7	V

Note: 1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to the absolute maximum rating conditions for extended periods of time may affect reliability.

2. Soldering temperature not to exceed 260°C for 10 seconds (total thermal budget not to exceed 150°C for longer than 30 seconds).

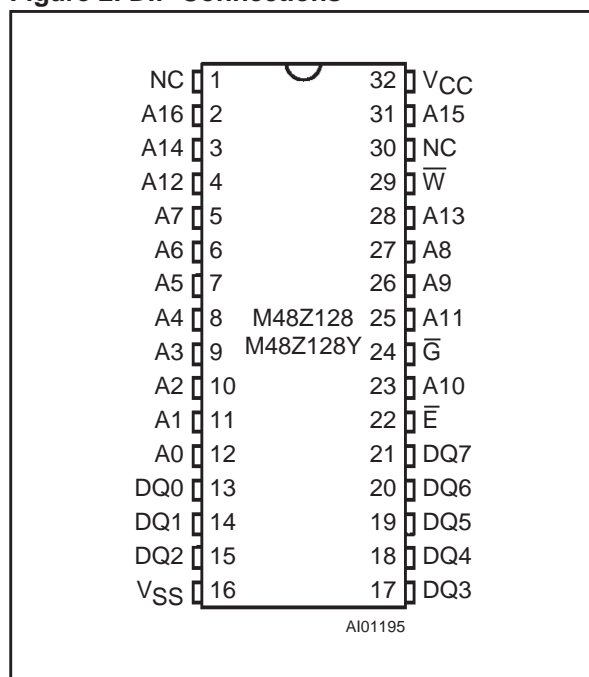
**CAUTION:** Negative undershoots below -0.3V are not allowed on any pin while in the Battery Back-up mode.

**Table 3. Operating Modes**

Mode	V <sub>CC</sub>	$\bar{E}$	$\bar{G}$	$\bar{W}$	DQ0-DQ7	Power
Deselect	4.75V to 5.5V or 4.5V to 5.5V	V <sub>IH</sub>	X	X	High Z	Standby
Write		V <sub>IL</sub>	X	V <sub>IL</sub>	D <sub>IN</sub>	Active
Read		V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	D <sub>OUT</sub>	Active
Read		V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	High Z	Active
Deselect	V <sub>SO</sub> to V <sub>PF</sub> D (min)	X	X	X	High Z	CMOS Standby
Deselect	≤ V <sub>SO</sub>	X	X	X	High Z	Battery Back-up Mode

Note: 1. X = V<sub>IH</sub> or V<sub>IL</sub>; V<sub>SO</sub> = Battery Back-up Switchover Voltage.

**Figure 2. DIP Connections**



## DESCRIPTION

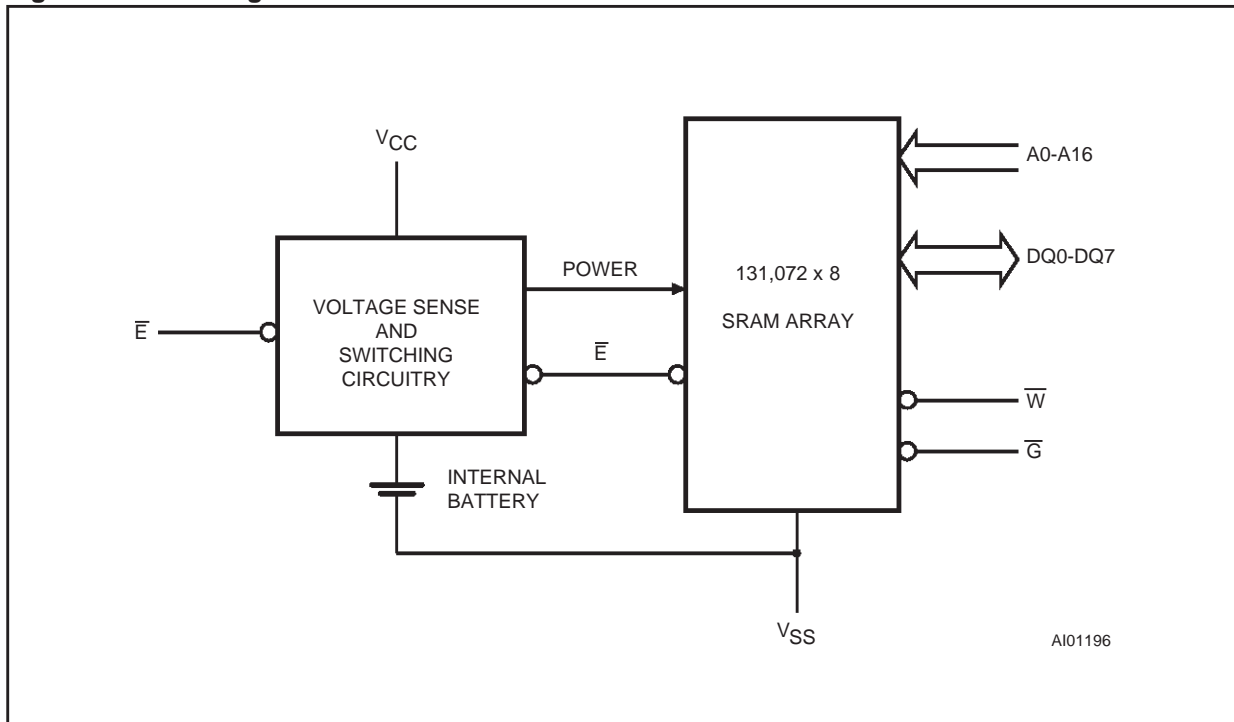
The M48Z128/128Y ZEROPOWER<sup>®</sup> RAM is a 128 Kbit x8 non-volatile static RAM that integrates power-fail deselect circuitry and battery control logic on a single die. The monolithic chip is available in two special packages to provide a highly integrated battery backed-up memory solution.

The M48Z128/128Y is a non-volatile pin and function equivalent to any JEDEC standard 128K x8 SRAM. It also easily fits into many ROM, EPROM, and EEPROM sockets, providing the non-volatility of PROMs without any requirement for special write timing or limitations on the number of writes that can be performed. The 32 pin 600mil DIP Module houses the M48Z128/128Y silicon with a long life lithium button cell in a single package.

For surface mount environments ST provides a Chip Set solution consisting of a 28 pin 330mil SOIC NVRAM Supervisor (M40Z300) and a 32 pin TSOP (8 x 20mm) LPSRAM (M68Z128) packages.

The 28 pin 330mil SOIC provides sockets with gold plated contacts at both ends for direct connection to a separate SNAPHAT housing containing the battery.

Figure 3. Block Diagram



The unique design allows the SNAPHAT battery package to be mounted on top of the SOIC package after the completion of the surface mount process. Insertion of the SNAPHAT housing after reflow prevents potential battery damage due to the high temperatures required for device surface-mounting. The SNAPHAT housing is keyed to prevent reverse insertion.

The SNAPHAT battery package is shipped separately in plastic anti-static tubes or in Tape & Reel form. The part number is "M4Z28-BRxxSH1".

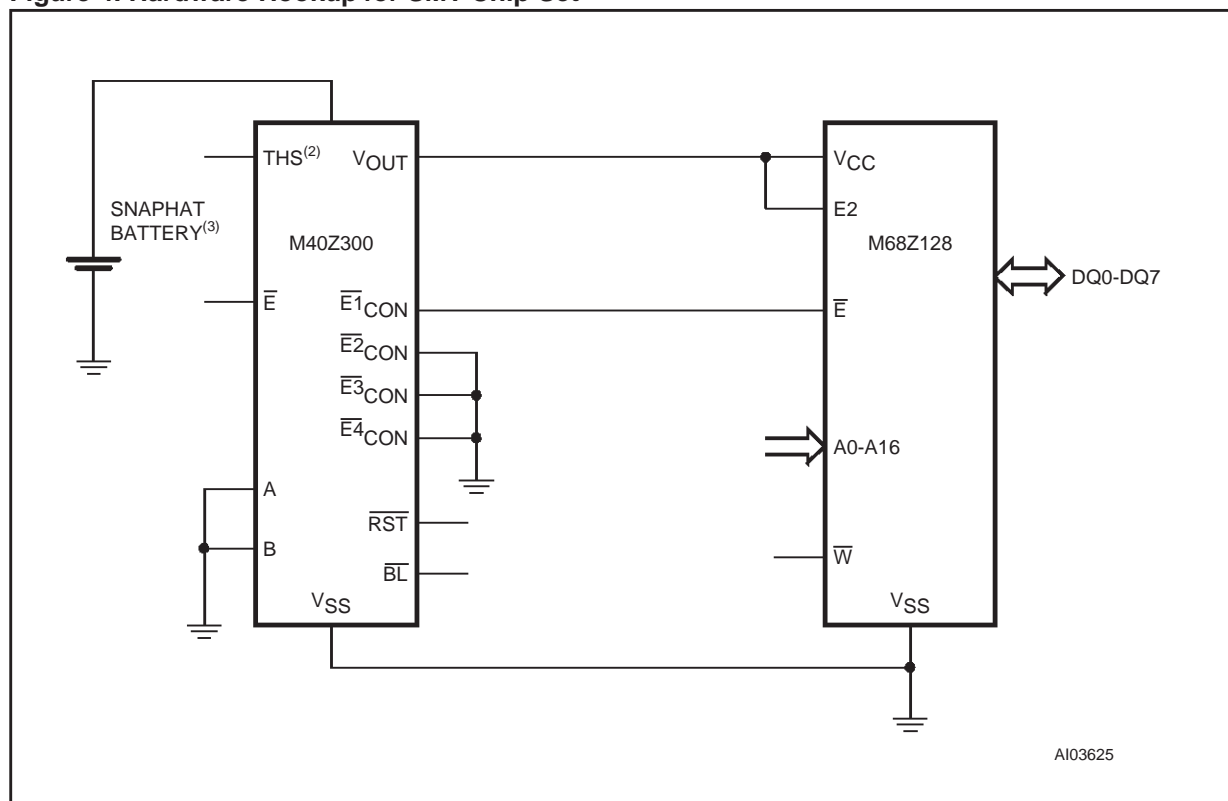
The M48Z128/128Y also has its own Power-fail Detect circuit. The control circuitry constantly monitors the single 5V supply for an out of tolerance condition. When  $V_{CC}$  is out of tolerance, the circuit write protects the SRAM, providing a high degree of data security in the midst of unpredictable system operation brought on by low  $V_{CC}$ . As  $V_{CC}$  falls below approximately 3V, the control circuitry connects the battery which maintains data until valid power returns.

### READ MODE

The M48Z128/128Y is in the Read Mode whenever  $\overline{W}$  (Write Enable) is high and  $\overline{E}$  (Chip Enable) is low. The device architecture allows ripple-through access of data from eight of 1,048,576 locations in the static storage array. Thus, the unique address specified by the 17 Address Inputs defines which one of the 131,072 bytes of data is to be accessed. Valid data will be available at the Data I/O pins within Address Access time ( $t_{AVQV}$ ) after the last address input signal is stable, providing that the  $\overline{E}$  and  $\overline{G}$  (Output Enable) access times are also satisfied. If the  $\overline{E}$  and  $\overline{G}$  access times are not met, valid data will be available after the later of Chip Enable Access time ( $t_{ELQV}$ ) or Output Enable Access Time ( $t_{GLQV}$ ). The state of the eight three-state Data I/O signals is controlled by  $\overline{E}$  and  $\overline{G}$ . If the outputs are activated before  $t_{AVQV}$ , the data lines will be driven to an indeterminate state until  $t_{AVQV}$ . If the Address Inputs are changed while  $\overline{E}$  and  $\overline{G}$  remain low, output data will remain valid for Output Data Hold time ( $t_{AXQX}$ ) but will go indeterminate until the next Address Access.

## M48Z128, M48Z128Y

Figure 4. Hardware Hookup for SMT Chip Set <sup>(1)</sup>



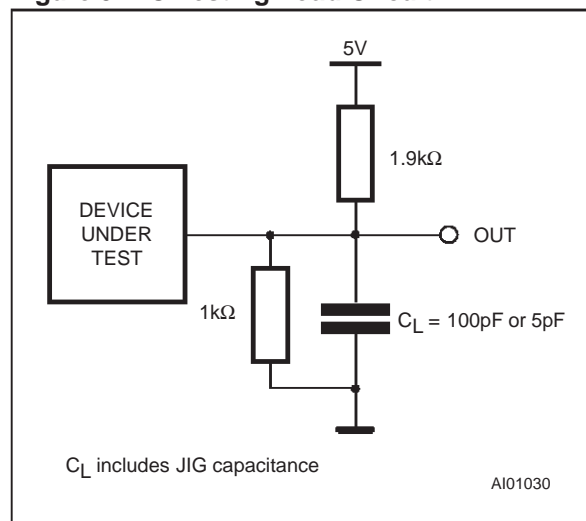
Note: 1. For pin connections, see individual data sheets for M40Z300 and M68Z128 at [www.st.com](http://www.st.com).  
 2. Connect THS pin to  $V_{OUT}$  if  $4.2V \leq V_{PFD} \leq 4.5V$  (M48Z128Y) or connect THS pin to  $V_{SS}$  if  $4.5V \leq V_{PFD} \leq 4.75V$  (M48Z128).  
 3. SNAPHAT ordered separately.

Table 4. AC Measurement Conditions

Input Rise and Fall Times	$\leq 5ns$
Input Pulse Voltages	0 to 3V
Input and Output Timing Ref. Voltages	1.5V

Note that Output Hi-Z is defined as the point where data is no longer driven.

Figure 5. AC Testing Load Circuit



**Table 5. Capacitance** <sup>(1, 2)</sup>  
 ( $T_A = 25\text{ }^\circ\text{C}$ ,  $f = 1\text{MHz}$ )

Symbol	Parameter	Test Condition	Min	Max	Unit
$C_{IN}$	Input Capacitance	$V_{IN} = 0V$		10	pF
$C_{IO}^{(3)}$	Input / Output Capacitance	$V_{OUT} = 0V$		10	pF

Note: 1. Effective capacitance measured with power supply at 5V.  
 2. Sampled only, not 100% tested.  
 3. Outputs deselected.

**Table 6. DC Characteristics**  
 ( $T_A = 0\text{ to }70\text{ }^\circ\text{C}$ ;  $V_{CC} = 4.75V\text{ to }5.5V\text{ or }4.5V\text{ to }5.5V$ )

Symbol	Parameter	Test Condition	Min	Max	Unit
$I_{LI}^{(1)}$	Input Leakage Current	$0V \leq V_{IN} \leq V_{CC}$		$\pm 1$	$\mu A$
$I_{LO}^{(1)}$	Output Leakage Current	$0V \leq V_{OUT} \leq V_{CC}$		$\pm 1$	$\mu A$
$I_{CC}$	Supply Current	$\bar{E} = V_{IL}$ , Outputs open		105	mA
$I_{CC1}$	Supply Current (Standby) TTL	$\bar{E} = V_{IH}$		7	mA
$I_{CC2}$	Supply Current (Standby) CMOS	$\bar{E} \geq V_{CC} - 0.2V$		4	mA
$V_{IL}$	Input Low Voltage		-0.3	0.8	V
$V_{IH}$	Input High Voltage		2.2	$V_{CC} + 0.3$	V
$V_{OL}$	Output Low Voltage	$I_{OL} = 2.1\text{mA}$		0.4	V
$V_{OH}$	Output High Voltage	$I_{OH} = -1\text{mA}$	2.4		V

Note: 1. Outputs deselected.

**Table 7. Power Down/Up Trip Points DC Characteristics** <sup>(1)</sup>  
 ( $T_A = 0\text{ to }70\text{ }^\circ\text{C}$ )

Symbol	Parameter	Min	Typ	Max	Unit	
$V_{PFD}$	Power-fail Deselect Voltage	M48Z128	4.5	4.6	4.75	V
		M48Z128Y	4.2	4.3	4.5	V
$V_{SO}$	Battery Back-up Switchover Voltage		3		V	
$t_{DR}^{(2)}$	Data Retention Time	10			YEARS	

Note: 1. All voltages referenced to  $V_{SS}$ .  
 2. At  $25\text{ }^\circ\text{C}$ .

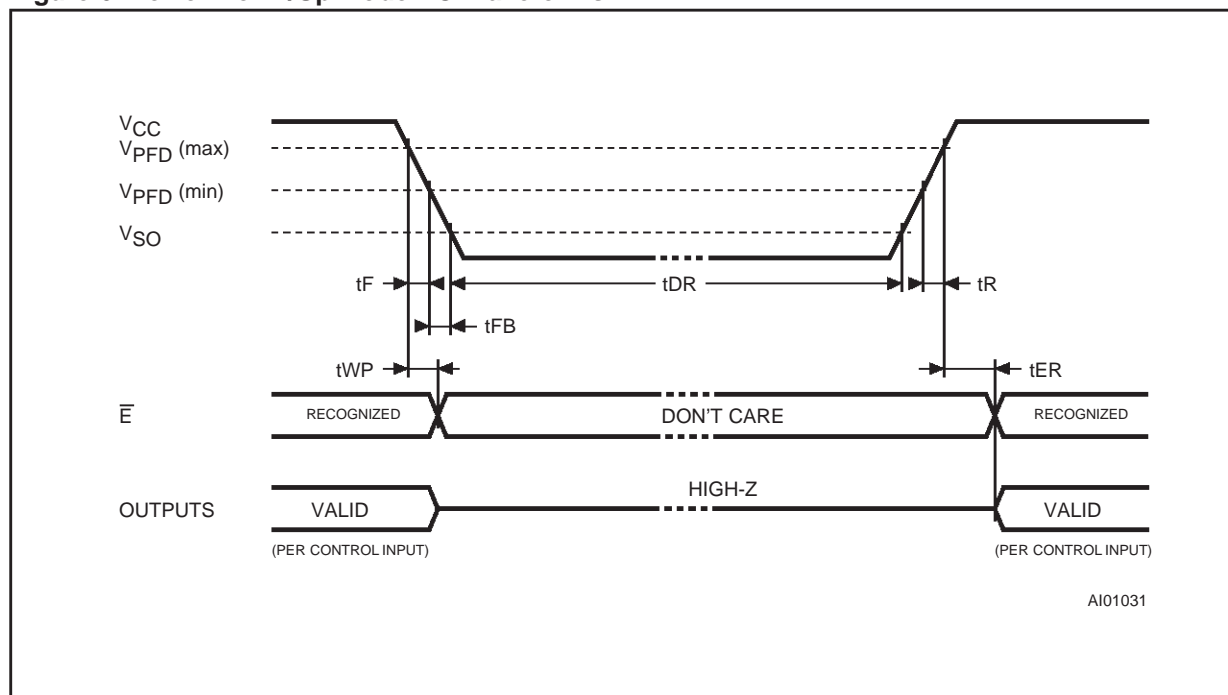
## M48Z128, M48Z128Y

**Table 8. Power Down/Up AC Characteristics**  
( $T_A = 0$  to  $70$  °C)

Symbol	Parameter	Min	Max	Unit
$t_F$ (1)	$V_{PFD}(\max)$ to $V_{PFD}(\min)$ $V_{CC}$ Fall Time	300		$\mu\text{s}$
$t_{FB}$ (2)	$V_{PFD}(\min)$ to $V_{SO}$ $V_{CC}$ Fall Time	10		$\mu\text{s}$
$t_{WP}$	Write Protect Time from $V_{CC} = V_{PFD}$	40	150	$\mu\text{s}$
$t_R$	$V_{SO}$ to $V_{PFD}(\max)$ $V_{CC}$ Rise Time	0		$\mu\text{s}$
$t_{ER}$	$\bar{E}$ Recovery Time	40	120	ms

Note: 1.  $V_{PFD}(\max)$  to  $V_{PFD}(\min)$  fall time of less than  $t_F$  may result in deselection/write protection not occurring until  $200\mu\text{s}$  after  $V_{CC}$  passes  $V_{PFD}(\min)$ .  
2.  $V_{PFD}(\min)$  to  $V_{SO}$  fall time of less than  $t_{FB}$  may cause corruption of RAM data.

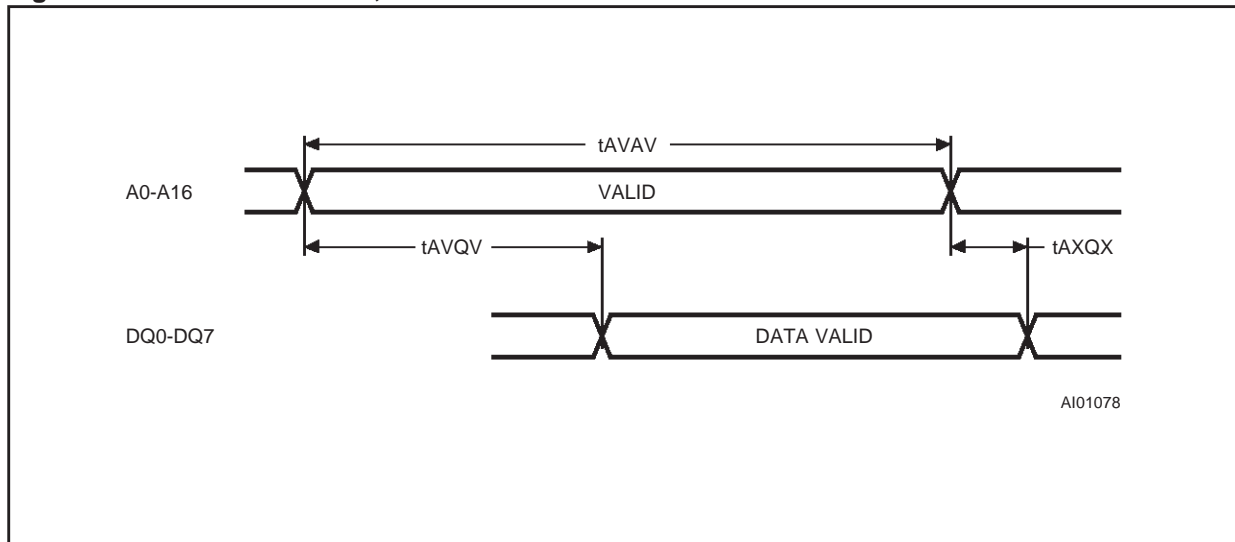
**Figure 6. Power Down/Up Mode AC Waveforms**



**Table 9. Read Mode AC Characteristics**(T<sub>A</sub> = 0 to 70 °C; V<sub>CC</sub> = 4.75V to 5.5V or 4.5V to 5.5V)

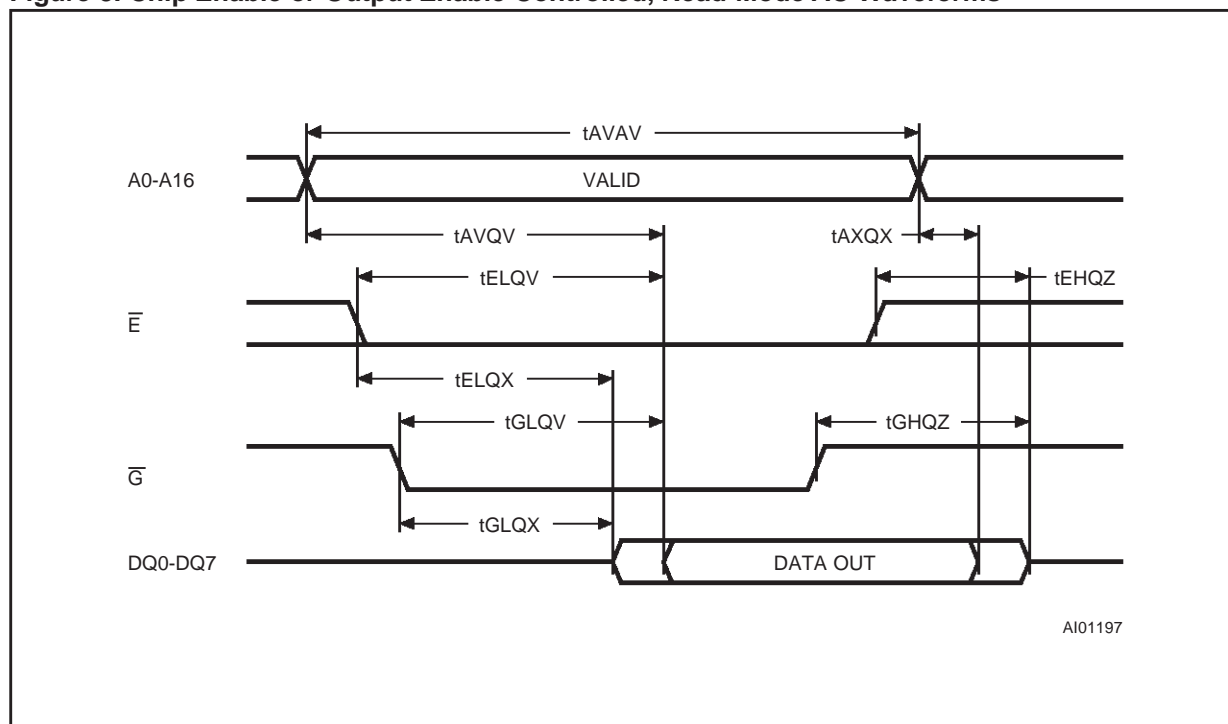
Symbol	Parameter	M48Z128/M48Z128Y						Unit
		-70		-85		-120		
		Min	Max	Min	Max	Min	Max	
t <sub>AVAV</sub>	Read Cycle Time	70		85		120		ns
t <sub>AVQV</sub> <sup>(1)</sup>	Address Valid to Output Valid		70		85		120	ns
t <sub>ELQV</sub> <sup>(1)</sup>	Chip Enable Low to Output Valid		70		85		120	ns
t <sub>GLQV</sub> <sup>(1)</sup>	Output Enable Low to Output Valid		35		45		60	ns
t <sub>ELQX</sub> <sup>(2)</sup>	Chip Enable Low to Output Transition	5		5		5		ns
t <sub>GLQX</sub> <sup>(2)</sup>	Output Enable Low to Output Transition	3		3		3		ns
t <sub>EHQZ</sub> <sup>(2)</sup>	Chip Enable High to Output Hi-Z		30		35		45	ns
t <sub>GHQZ</sub> <sup>(2)</sup>	Output Enable High to Output Hi-Z		20		25		35	ns
t <sub>AXQX</sub> <sup>(1)</sup>	Address Transition to Output Transition	5		5		10		ns

Note: 1. C<sub>L</sub> = 100pF.  
2. C<sub>L</sub> = 5pF.

**Figure 7. Address Controlled, Read Mode AC Waveforms**

Note: Chip Enable ( $\overline{E}$ ) and Output Enable ( $\overline{G}$ ) = Low, Write Enable ( $\overline{W}$ ) = High.

Figure 8. Chip Enable or Output Enable Controlled, Read Mode AC Waveforms



Note: Write Enable ( $\bar{W}$ ) = High.

### WRITE MODE

The M48Z128/128Y is in the Write Mode whenever  $\bar{W}$  and  $\bar{E}$  are active. The start of a write is referenced from the latter occurring falling edge of  $\bar{W}$  or  $\bar{E}$ . A write is terminated by the earlier rising edge of  $\bar{W}$  or  $\bar{E}$ .

The addresses must be held valid throughout the cycle.  $\bar{E}$  or  $\bar{W}$  must return high for minimum of  $t_{EHAX}$  from  $\bar{E}$  or  $t_{WHAX}$  from  $\bar{W}$  prior to the initiation of another read or write cycle. Data-in must be valid  $t_{DVWH}$  prior to the end of write and remain valid for  $t_{WHDX}$  or  $t_{EHDX}$  afterward.  $\bar{G}$  should be kept high during write cycles to avoid bus contention; although, if the output bus has been activated by a low on  $\bar{E}$  and  $\bar{G}$ , a low on  $\bar{W}$  will disable the outputs  $t_{WLQZ}$  after  $\bar{W}$  falls.

### DATA RETENTION MODE

With valid  $V_{CC}$  applied, the M48Z128/128Y operates as a conventional BYTEWIDE™ static RAM. Should the supply voltage decay, the RAM will automatically power-fail deselect, write protecting it-

self  $t_{WP}$  after  $V_{CC}$  falls below  $V_{PFD}$ . All outputs become high impedance, and all inputs are treated as "don't care."

If power fail detection occurs during a valid access, the memory cycle continues to completion. If the memory cycle fails to terminate within the time  $t_{WP}$ , write protection takes place. When  $V_{CC}$  drops below  $V_{SO}$ , the control circuit switches power to the internal energy source which preserves data.

The internal coin cell will maintain data in the M48Z128/128Y after the initial application of  $V_{CC}$  for an accumulated period of at least 10 years when  $V_{CC}$  is less than  $V_{SO}$ . As system power returns and  $V_{CC}$  rises above  $V_{SO}$ , the battery is disconnected, and the power supply is switched to external  $V_{CC}$ . Write protection continues for  $t_{ER}$  after  $V_{CC}$  reaches  $V_{PFD}$  to allow for processor stabilization. After  $t_{ER}$ , normal RAM operation can resume.

For more information on Battery Storage Life refer to the Application Note AN1012.



**Table 10. Write Mode AC Characteristics**  
( $T_A = 0$  to  $70$  °C;  $V_{CC} = 4.75V$  to  $5.5V$  or  $4.5V$  to  $5.5V$ )

Symbol	Parameter	M48Z128/M48Z128Y						Unit
		-70		-85		-120		
		Min	Max	Min	Max	Min	Max	
$t_{AVAV}$	Write Cycle Time	70		85		120		ns
$t_{AVWL}$	Address Valid to Write Enable Low	0		0		0		ns
$t_{AVEL}$	Address Valid to Chip Enable Low	0		0		0		ns
$t_{WLWH}$	Write Enable Pulse Width	55		65		85		ns
$t_{ELEH}$	Chip Enable Low to Chip Enable High	55		75		100		ns
$t_{WHAX}$	Write Enable High to Address Transition	5		5		5		ns
$t_{EHAX}$	Chip Enable High to Address Transition	15		15		15		ns
$t_{DVWH}$	Input Valid to Write Enable High	30		35		45		ns
$t_{DVEH}$	Input Valid to Chip Enable High	30		35		45		ns
$t_{WHDX}$	Write Enable High to Input Transition	0		0		0		ns
$t_{EHDX}$	Chip Enable High to Input Transition	10		10		10		ns
$t_{WLQZ}^{(1, 2)}$	Write Enable Low to Output Hi-Z		25		30		40	ns
$t_{AVWH}$	Address Valid to Write Enable High	65		75		100		ns
$t_{AVEH}$	Address Valid to Chip Enable High	65		75		100		ns
$t_{WHQX}^{(1, 2)}$	Write Enable High to Output Transition	5		5		5		ns

Note: 1.  $C_L = 5pF$ .

2. If  $\bar{E}$  goes low simultaneously with  $\bar{W}$  going low after  $\bar{W}$  going low, the outputs remain in the high impedance state.

### POWER SUPPLY DECOUPLING and UNDERSHOOT PROTECTION

$I_{CC}$  transients, including those produced by output switching, can produce voltage fluctuations, resulting in spikes on the  $V_{CC}$  bus. These transients can be reduced if capacitors are used to store energy, which stabilizes the  $V_{CC}$  bus. The energy stored in the bypass capacitors will be released as low going spikes are generated or energy will be absorbed when overshoots occur. A ceramic bypass capacitor value of  $0.1\mu F$  (as shown in Figure 9) is recommended in order to provide the needed filtering.

In addition to transients that are caused by normal SRAM operation, power cycling can generate negative voltage spikes on  $V_{CC}$  that drive it to values below  $V_{SS}$  by as much as one Volt. These negative spikes can cause data corruption in the SRAM while in battery backup mode. To protect from these voltage spikes, it is recommended to connect a schottky diode from  $V_{CC}$  to  $V_{SS}$  (cathode connected to  $V_{CC}$ , anode to  $V_{SS}$ ). Schottky diode 1N5817 is recommended for through hole and MBR5120T3 is recommended for surface mount.

**Figure 9. Supply Voltage Protection**

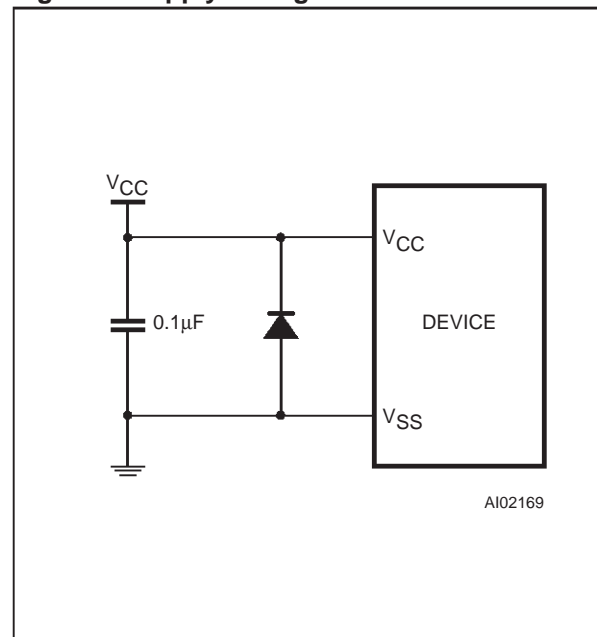
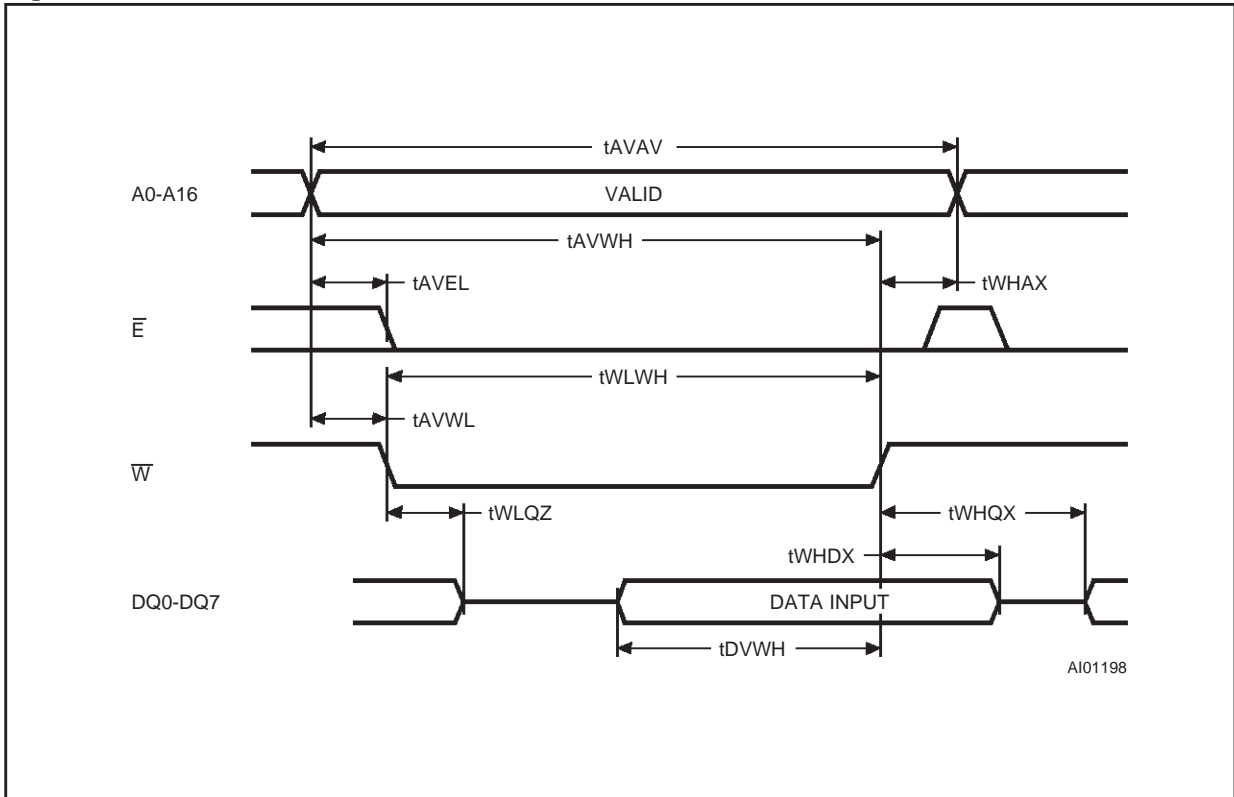
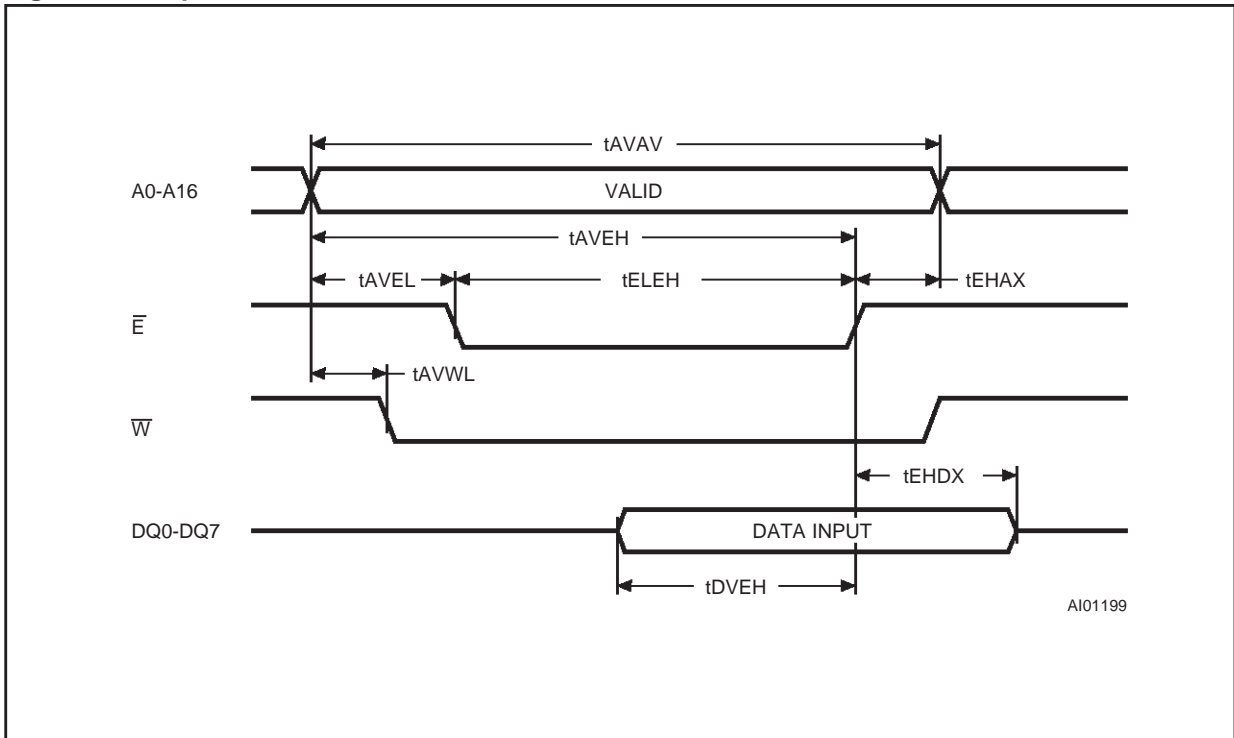


Figure 10. Write Enable Controlled, Write AC Waveforms



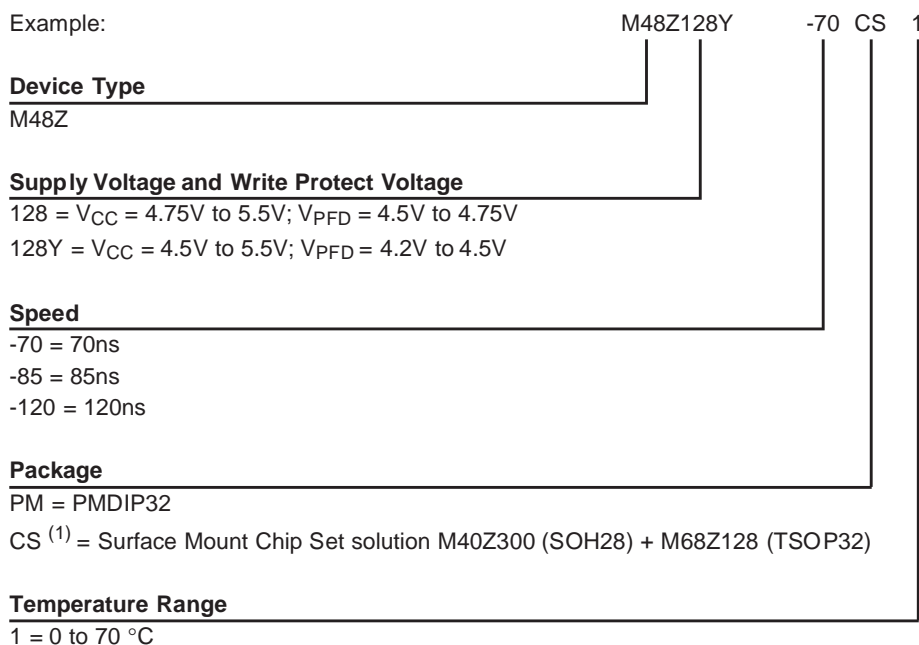
Note: Output Enable ( $\bar{G}$ ) = High.

Figure 11. Chip Enable Controlled, Write AC Waveforms



Note: Output Enable ( $\bar{G}$ ) = High.

**Table 11. Ordering Information Scheme**



Note: 1. The SOIC package (SOH28) requires the battery package (SNAPHAT) which is ordered separately under the part number "M4Zxx-BR00SH1" in plastic tube or "M4Zxx-BR00SH1TR" in Tape & Reel form.

**Caution:** Do not place the SNAPHAT battery package "M4Zxx-BR00SH1" in conductive foam since this will drain the lithium button-cell battery.

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.

**Table 12. Revision History**

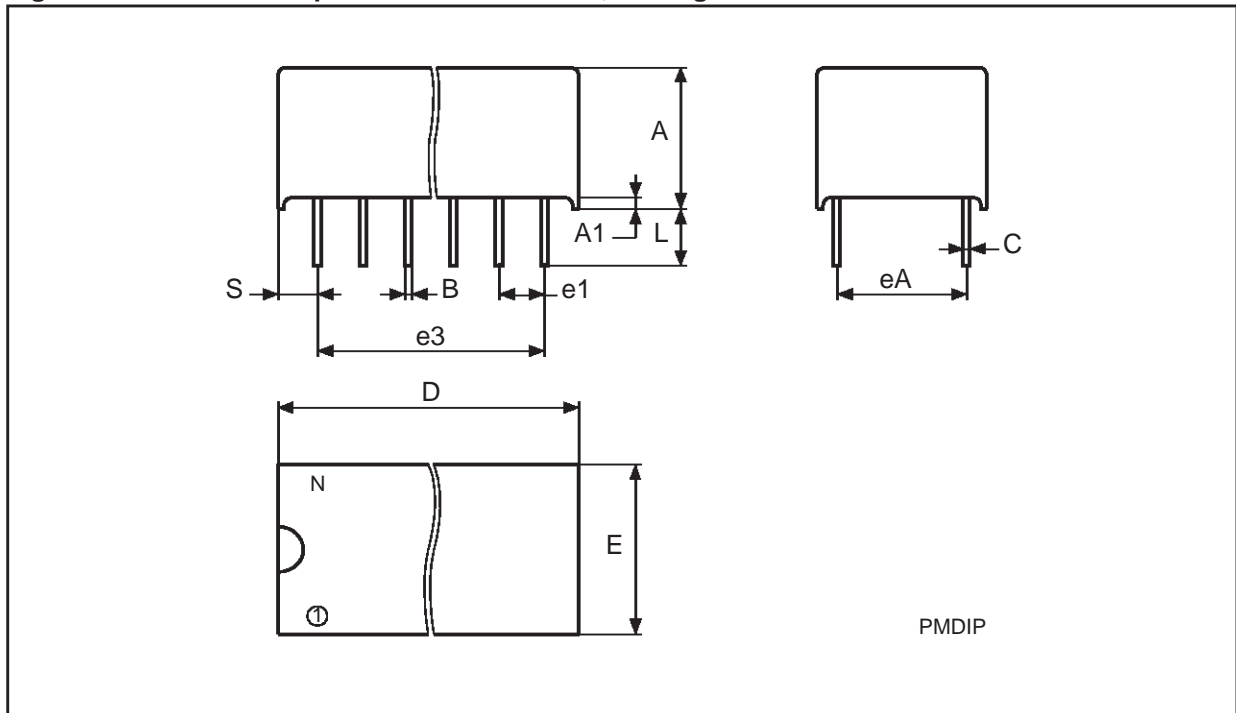
Date	Revision Details
May 1999	First Issue
04/13/00	Document Layout changed Surface Mount Chip Set solution added
06/20/00	t <sub>GLQX</sub> changed (Table 9)

**M48Z128, M48Z128Y**

**Table 13. PMDIP32 - 32 pin Plastic Module DIP, Package Mechanical Data**

Symbol	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A		9.27	9.52		0.365	0.375
A1		0.38			0.015	
B		0.43	0.59		0.017	0.023
C		0.20	0.33		0.008	0.013
D		42.42	43.18		1.670	1.700
E		18.03	18.80		0.710	0.740
e1		2.29	2.79		0.090	0.110
e3		34.29	41.91		1.350	1.650
eA		14.99	16.00		0.590	0.630
L		3.05	3.81		0.120	0.150
S		1.91	2.79		0.075	0.110
N		32			32	

**Figure 12. PMDIP32 - 32 pin Plastic Module DIP, Package Outline**

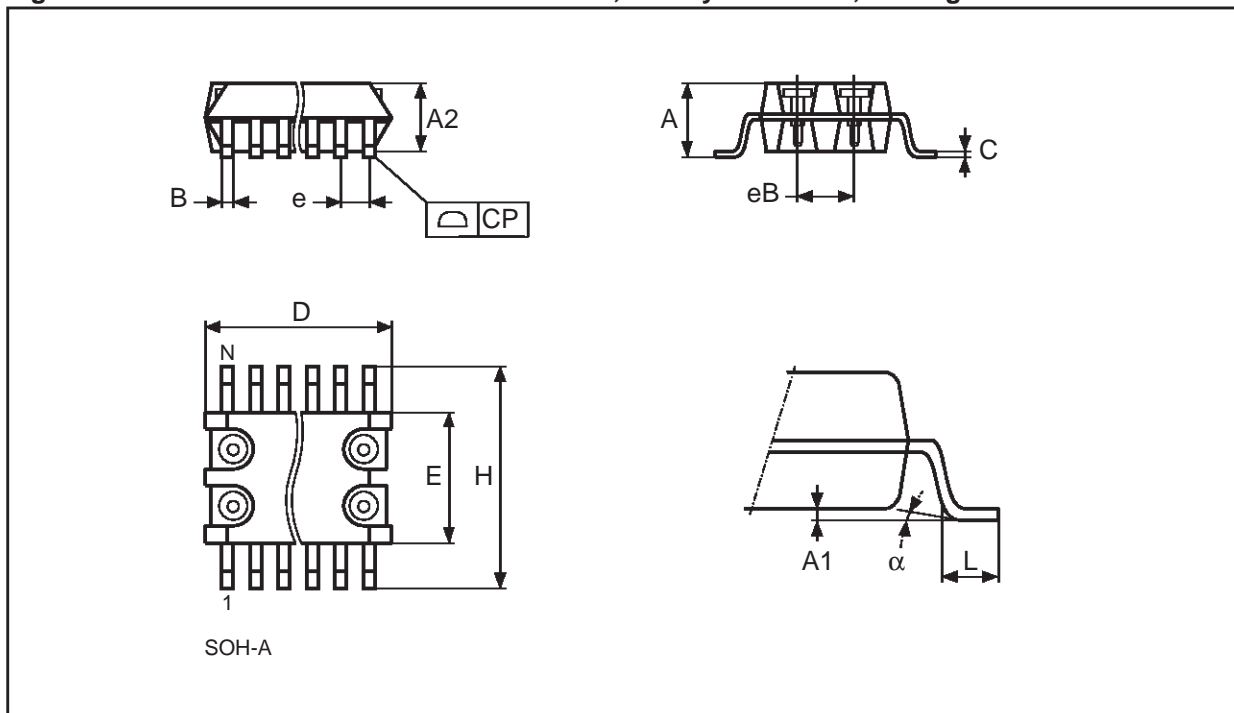


Drawing is not to scale.

Table 14. SOH28 - 28 lead Plastic Small Outline, battery SNAPHAT, Package Mechanical Data

Symbol	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A			3.05			0.120
A1		0.05	0.36		0.002	0.014
A2		2.34	2.69		0.092	0.106
B		0.36	0.51		0.014	0.020
C		0.15	0.32		0.006	0.012
D		17.71	18.49		0.697	0.728
E		8.23	8.89		0.324	0.350
e	1.27	–	–	0.050	–	–
eB		3.20	3.61		0.126	0.142
H		11.51	12.70		0.453	0.500
L		0.41	1.27		0.016	0.050
$\alpha$		0°	8°		0°	8°
N		28			28	
CP			0.10			0.004

Figure 13. SOH28 - 28 lead Plastic Small Outline, battery SNAPHAT, Package Outline



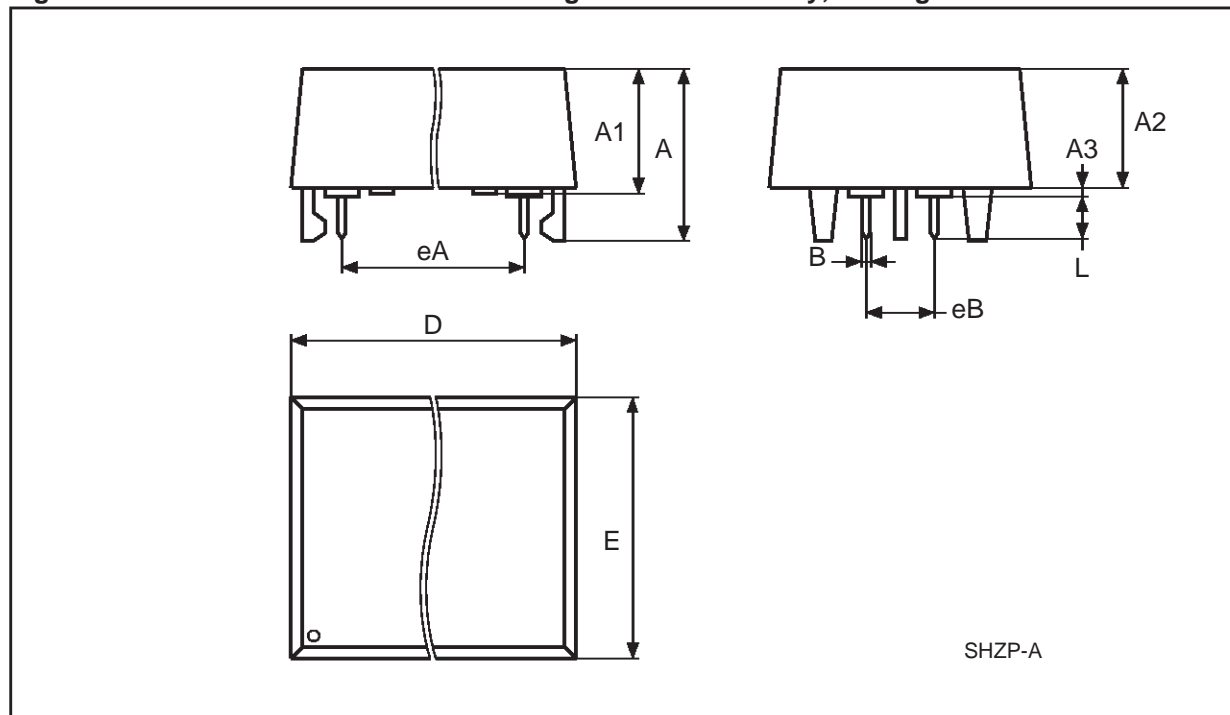
Drawing is not to scale.

**M48Z128, M48Z128Y**

**Table 15. M4Z28-BR00SH SNAPHAT Housing for 48 mAh Battery, Package Mechanical Data**

Symbol	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A			9.78			0.385
A1		6.73	7.24		0.265	0.285
A2		6.48	6.99		0.255	0.275
A3			0.38			0.015
B		0.46	0.56		0.018	0.022
D		21.21	21.84		0.835	0.860
E		14.22	14.99		0.560	0.590
eA		15.55	15.95		0.612	0.628
eB		3.20	3.61		0.126	0.142
L		2.03	2.29		0.080	0.090

**Figure 14. M4Z28-BR00SH SNAPHAT Housing for 48 mAh Battery, Package Outline**

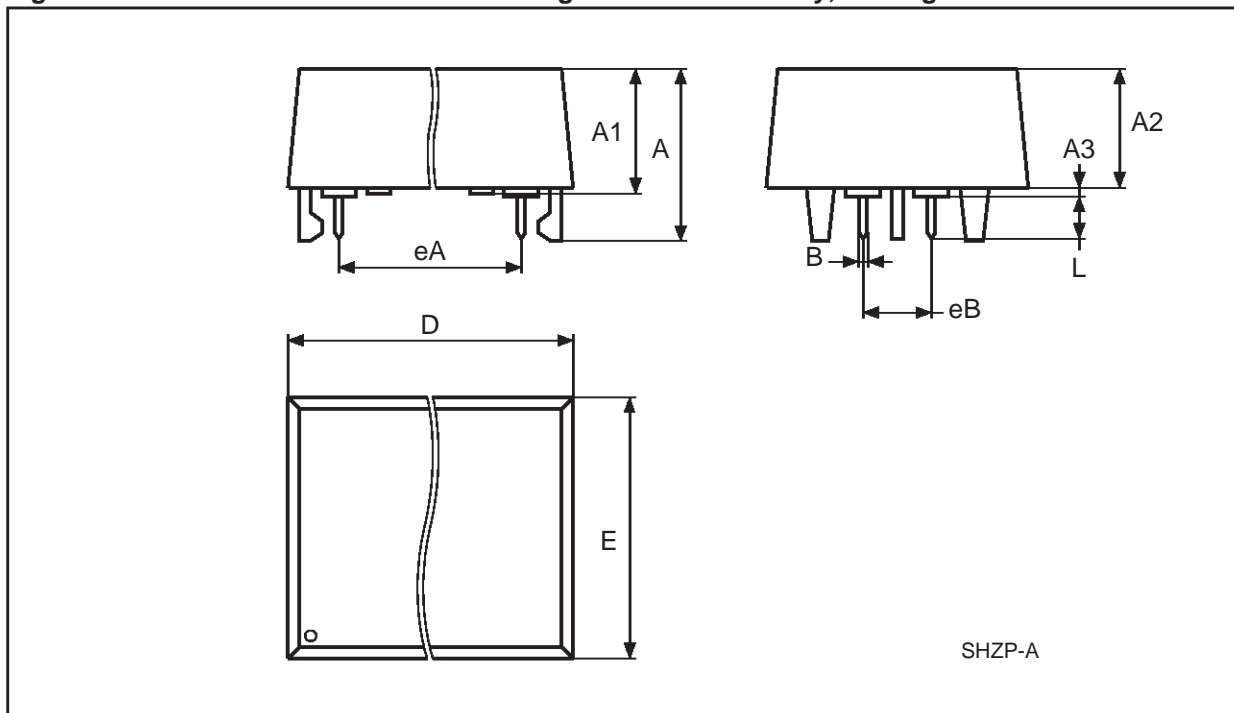


Drawing is not to scale.

Table 16. M4Z32-BR00SH SNAPHAT Housing for 120 mAh Battery, Package Mechanical Data

Symbol	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A			10.54			0.415
A1		8.00	8.51		0.315	0.335
A2		7.24	8.00		0.285	0.315
A3			0.38			0.015
B		0.46	0.56		0.018	0.022
D		21.21	21.84		0.835	0.860
E		17.27	18.03		0.680	0.710
eA		15.55	15.95		0.612	0.628
eB		3.20	3.61		0.126	0.142
L		2.03	2.29		0.080	0.090

Figure 15. M4Z32-BR00SH SNAPHAT Housing for 120 mAh Battery, Package Outline



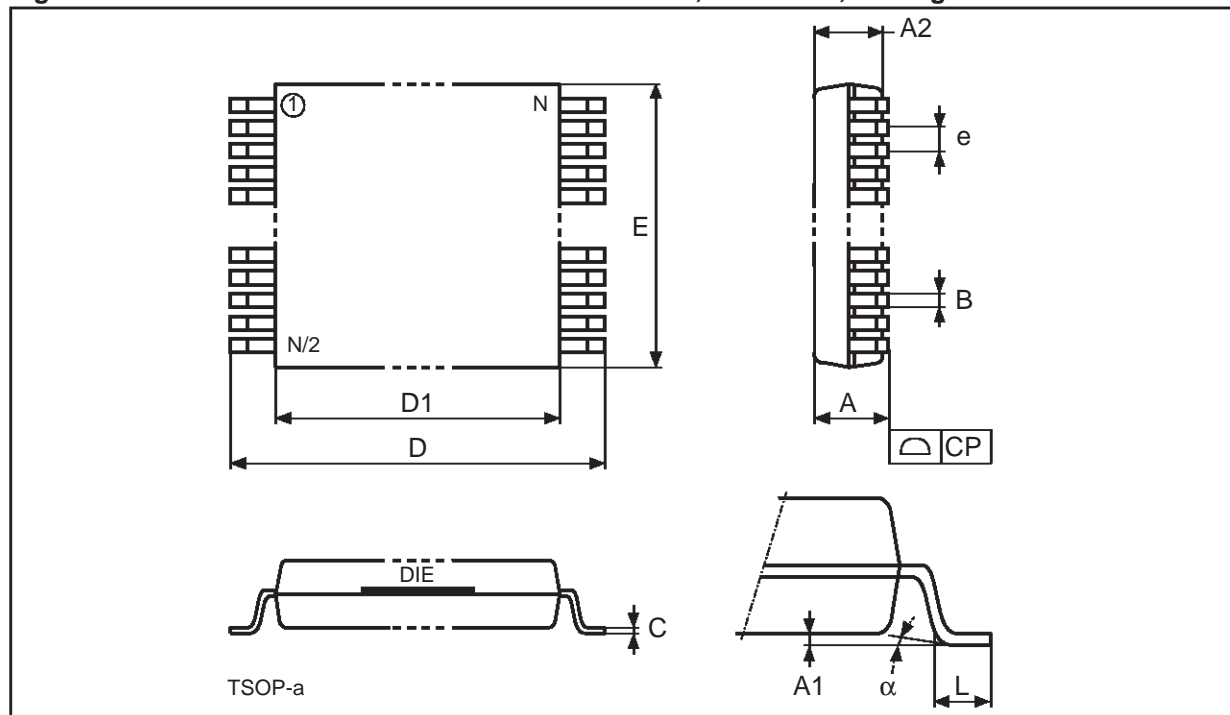
Drawing is not to scale.

**M48Z128, M48Z128Y**

**Table 17. TSOP32 - 32 lead Plastic Thin Small Outline, 8 x 20 mm, Package Mechanical Data**

Symbol	mm			inch		
	Typ	Min	Max	Typ	Min	Max
A			1.200			0.0472
A1		0.050	0.150		0.0020	0.0059
A2		0.950	1.050		0.0374	0.0413
B		0.150	0.270		0.0059	0.0106
C		0.100	0.210		0.0039	0.0083
D		19.800	20.200		0.7795	0.7953
D1		18.300	18.500		0.7205	0.7283
e	0.500	–	–	0.0197	–	–
E		7.900	8.100		0.3110	0.3189
L		0.500	0.700		0.0197	0.0276
$\alpha$		0°	5°		0°	5°
CP			0.100			0.0039
N		32			32	

**Figure 16. TSOP32 - 32 lead Plastic Thin Small Outline, 8 x 20 mm, Package Outline**



Drawing is not to scale.



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